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Chalcogenide Photovoltaics

Physics, Technologies, and Thin Film Devices



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Contents

	Preface	<i>XI</i>
	Symbols and Acronyms	<i>XIII</i>
1	Introduction	<i>1</i>
1.1	History of Cu(In,Ga)(S,Se) ₂ Solar Cells	<i>1</i>
1.1.1	Milestones of Cu(In,Ga)(S,Se) ₂ Development	<i>3</i>
1.2	History of CdTe Solar Cells	<i>5</i>
1.2.1	Milestones of CdTe Development	<i>6</i>
1.3	Prospects of Chalcogenide Photovoltaics	<i>7</i>
2	Thin Film Heterostructures	<i>9</i>
2.1	Energies and Potentials	<i>9</i>
2.2	Charge Densities and Fluxes	<i>11</i>
2.3	Energy Band Diagrams	<i>13</i>
2.3.1	Rules and Conventions	<i>13</i>
2.3.2	Absorber/Window	<i>17</i>
2.3.3	Absorber/Buffer/Window	<i>20</i>
2.3.4	Interface States	<i>24</i>
2.3.5	Interface Dipoles	<i>29</i>
2.3.6	Deep Bulk States	<i>29</i>
2.3.7	Bandgap Gradients	<i>32</i>
2.4	Diode Currents	<i>36</i>
2.4.1	Superposition Principle and Shifting Approximation	<i>36</i>
2.4.2	Regions of Recombination	<i>37</i>
2.4.3	Radiative Recombination	<i>40</i>
2.4.4	Auger Recombination	<i>43</i>
2.4.5	Defect Related Recombination	<i>44</i>
2.4.5.1	SCR Recombination	<i>50</i>
2.4.5.2	QNR Recombination	<i>60</i>
2.4.5.3	Back Surface Recombination	<i>62</i>
2.4.5.4	Interface Recombination	<i>63</i>
2.4.6	Parallel Processes	<i>73</i>
2.4.6.1	SCR and QNR Recombination	<i>73</i>

2.4.6.2	SCR and IF Recombination	75
2.4.7	Barriers for Diode Current	76
2.4.8	Bias Dependence	78
2.4.9	Non-Homogeneities	79
2.5	Light Generated Currents	80
2.5.1	Generation Currents	81
2.5.2	Generation Function	84
2.5.3	Photo Current	86
2.5.4	Collection Function	87
2.5.4.1	Absorber Quasi Neutral Region	87
2.5.4.2	QNR with Graded Bandgap	90
2.5.4.3	QNR with Back Surface Field	91
2.5.4.4	Absorber Space Charge Region	92
2.5.4.5	Buffer Layer	94
2.5.4.6	Simulating the Collection Function	95
2.5.5	Quantum Efficiency and Charge Collection Efficiency	96
2.5.6	Barriers for Photo Current	97
2.5.7	Voltage Dependence of Photo Current	99
2.5.7.1	Width of SCR	99
2.5.7.2	Interface Recombination	100
2.5.7.3	Photo Current Barriers	100
2.6	Device Analysis and Parameters	101
2.6.1	Equivalent Circuits	101
2.6.1.1	DC Equivalent Circuit	101
2.6.1.2	AC Equivalent Circuit	103
2.6.1.3	Module Equivalent Circuit	105
2.6.2	Current–Voltage Analysis	107
2.6.2.1	External Collection Efficiency	107
2.6.2.2	Diode Parameters	108
2.6.2.3	Open Circuit Voltage	112
2.6.2.4	Fill Factor	116
2.6.3	Capacitance–Voltage Analysis	119
2.6.4	Admittance Spectroscopy	122
3	Design Rules for Heterostructure Solar Cells and Modules	129
3.1	Absorber Bandgap	129
3.2	Band Alignment	131
3.3	Emitter Doping and Doping Ratio	137
3.4	Fermi Level Pinning	140
3.5	Absorber Doping	142
3.6	Absorber Thickness	147
3.7	Grain Boundaries	150
3.8	Back Contact Barrier	156
3.9	Buffer Thickness	159
3.10	Front Surface Gradient	162

3.11	Back Surface Gradients	165
3.12	Monolithic Series Interconnection	171
4	Thin Film Material Properties	175
4.1	$A^{II}-B^{VI}$ Absorbers	175
4.1.1	Physico-Chemical Properties	175
4.1.2	Lattice Dynamics	179
4.1.3	Electronic Properties	180
4.1.3.1	Practical Doping Limits	180
4.1.3.2	Defect Spectroscopy	182
4.1.3.3	Minority Carrier Lifetime	182
4.1.4	Optical Properties	185
4.1.4.1	CdTe	185
4.1.4.2	Multinary Phases	187
4.1.5	Surface Properties	188
4.1.6	Properties of Grain Boundaries	189
4.2	$A^I-B^{III}-C_2^{VI}$ Absorbers	192
4.2.1	Physico-Chemical Properties	193
4.2.1.1	Ternary Phase Diagrams	193
4.2.1.2	Multinary Phases	198
4.2.1.3	Diffusion Coefficients	200
4.2.2	Lattice Dynamics	201
4.2.3	Electronic Properties	203
4.2.3.1	Single Point Defects	204
4.2.3.2	Defect Complexes	209
4.2.3.3	Defect Spectroscopy	210
4.2.3.4	Practical Doping Limits	214
4.2.3.5	Carrier Mobility	215
4.2.3.6	Minority Carrier Lifetime	216
4.2.4	Optical Properties	216
4.2.4.1	Ternary Semiconductors	217
4.2.4.2	Multinary Semiconductors	218
4.2.5	Surface Properties	220
4.2.5.1	Surface Composition	220
4.2.5.2	Surface Electronics	222
4.2.6	Properties of Grain Boundaries	224
4.3	Buffer Layers	226
4.4	Window Layers	226
4.4.1	Low Resistance Windows	226
4.4.2	High Resistance Windows	230
4.5	Interfaces	230
5	Thin Film Technology	235
5.1	CdTe Cells and Modules	235
5.1.1	Substrates	235

5.1.2	Window Layers for CdTe Cells	236
5.1.3	Buffer Layers for CdTe Cells	237
5.1.4	CdTe Absorber Layer	240
5.1.5	Activation by Chlorine Treatment	243
5.1.6	Influence of Oxygen	245
5.1.7	Influence of Copper	246
5.1.8	Back Contact	249
5.1.8.1	Surface Modification	249
5.1.8.2	Primary and Secondary Contacts	250
5.1.9	Module Fabrication and Life Cycle Analysis	251
5.2	Cu(In,Ga)(S,Se) ₂ Cells and Modules	252
5.2.1	Substrates	253
5.2.2	Back Contacts	253
5.2.3	Cu(In,Ga)(S,Se) ₂ Absorber Layers	255
5.2.3.1	Co-evaporation	257
5.2.3.2	Deposition Reaction	260
5.2.3.3	Sputtering	262
5.2.3.4	Epitaxy, Chemical Vapor Deposition, and Vapor Transport Processes	262
5.2.4	Influence of Sodium	262
5.2.5	Influence of Gallium	265
5.2.6	Influence of Sulfur	265
5.2.7	Influence of Oxygen	266
5.2.8	Buffer Layers of CIGS	268
5.2.8.1	Chemical Bath Deposited CdS	268
5.2.8.2	Alternative Buffer Layers	270
5.2.9	Window Layers of CIGS	272
5.2.10	Module Fabrication	273
6	Photovoltaic Properties of Standard Devices	277
6.1	CdTe Device Properties	277
6.1.1	Solar Cell Parameters	277
6.1.2	Diode Currents	277
6.1.3	Collection Functions	279
6.1.4	Device Anomalies	280
6.1.5	Transient Effects and Metastability	281
6.1.6	Device Model	282
6.1.7	Stability	285
6.2	A ^I -B ^{III} -C ₂ ^{VI} Device Properties	286
6.2.1	Solar Cell Parameters	286
6.2.2	Diode Currents	288
6.2.3	Collection Function	290
6.2.4	Transient Effects and Metastability	292
6.2.4.1	Relaxed State	292
6.2.4.2	Models for Relaxed State	293

6.2.4.3	Red Light Effect	294
6.2.4.4	Forward Bias Effect	295
6.2.4.5	Blue Light Effect	295
6.2.4.6	White Light Effect	296
6.2.4.7	Reverse Bias Effect	296
6.2.4.8	Models for Metastability	297
6.2.4.9	Implications for Module Testing	298
6.2.5	Device Model	299
6.2.6	Stability	302
7	Appendix A: Frequently Observed Anomalies	305
7.1	JV Curves	305
7.1.1	Roll Over Effect	305
7.1.2	Cross Over	306
7.1.3	Kink in Light JV Curve	306
7.1.4	Violation of Shifting Approximation	307
7.2	Solar Cell Parameters	308
7.2.1	Reduced J_{sc} but High V_{oc}	308
7.2.2	Reduced V_{oc} but High J_{sc}	308
7.2.3	High J_{sc} but Low FF	309
7.3	Diode Parameters	309
7.3.1	Diode Parameter $A > 2$	309
7.3.2	Activation Energy $E_a < E_{g,a}$	309
7.3.3	Diode Quality Factor Illumination Dependent	310
7.3.4	Diode Quality Factor Temperature-Dependent	310
7.4	Quantum Efficiency	311
7.4.1	High J_{sc} but Low EQE	311
7.4.2	Low J_{sc} but High EQE	311
7.4.3	Low Blue Response in IQE	311
7.4.4	Low Red Response in IQE	312
7.4.5	Quantum Efficiency Low at All Wavelengths	312
7.4.6	Apparent Quantum Efficiency	313
7.5	Transient Effects	313
7.5.1	V_{oc} Time-Dependent with $dV_{oc}/dt > 0$	313
7.5.2	V_{oc} Time-Dependent with $dV_{oc}/dt < 0$	314
8	Appendix B: Tables	315
	References	321
	Index	361